

**John D. Cressler** received his Ph.D. from Columbia University in 1990. He was at IBM Research from 1984 to 1992, and on the faculty of Auburn University from 1992 to 2002. Since 2002 he has been on the faculty of Georgia Tech, where he is currently Ken Byers Professor of Electrical and Computer Engineering. His research interests include: Si-based (SiGe/strained-Si) heterostructure devices and technology, mixed-signal circuits built from these devices, radiation effects, cryogenic electronics, device-to-circuit interactions, noise and reliability physics, device-level simulation, and compact circuit modeling. He has published over 450 scientific papers related to his research, and is the co-author of Silicon-Germanium Heterojunction Bipolar Transistors (2003), the author of Reinventing Teenagers: the Gentle Art of Instilling Character in Our Young People (2004), the editor of The Silicon Heterostructure Handbook: Materials, Fabrication, Devices, Circuits, and Applications of SiGe and Si Strained-Layer Epitaxy (2006), and the author of Silicon Earth: Introduction to the Microelectronics and Nanotechnology Revolution (2009). During his academic career he has graduated 25 Ph.D. students and 23 M.S. students. He has served as associate editor for the *IEEE Journal of Solid-State Circuits*, the *IEEE Transactions on Nuclear Science*, and the *IEEE Transactions on Electron Devices*. He has been active on numerous conference program committees, including as the Technical Program Chair of the 1998 ISSCC and 2007 NSREC. He has received a number of awards for both his teaching and research, and is an IEEE Fellow.

